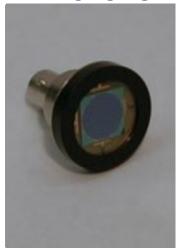
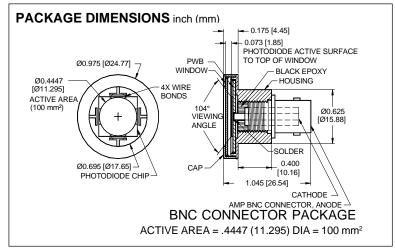
PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive DETECTORS INC. Type PDB-C112





FEATURES

- Blue enhanced
- Photoconductive
- High speed
- Low dark current

DESCRIPTION

Large area, instrumentation grade, blue enhanced silicon photodiode. Designed for low capacitance high speed photoconductive applications. Packaged in a BNC connector package.

APPLICATIONS

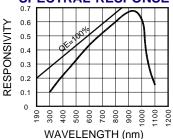
- Instrumentation
- Power meters
- Colorimeters
- Laser power meters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
VBR	Reverse Voltage		100	V	
TS	Storage Temperature	-20	+70	°C	
ТО	Operating Temperature Range	-10	+60	°C	
TS	Soldering Temperature*	N/A	N/A	°C	
lmax	Light Current		0.5	mA	

^{*1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ISC	Short Circuit Current	H = 100 fc, 2850 K	1.0	1.3		mA
ID	Dark Current	H = 0, VR = 10V		10	30	nA
RSH	Shunt Resistance	H = 0, VR = 10 mV	15	30		ΜΩ
TC RSH	RSH Temp. Coefficient	H = 0, VR = 10 mV		-8		%/°C
CJ	Junction Capacitance	H = 0, VR = 10V**		300		pF
Irange	Spectral Application Range	Spot Scan	350		1100	nm
lp	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I= 10 μA	30	50		V
NEP	Noise Equivalent Power	VR = 10 @ Peak		3x10 ⁻¹³		W/ √Hz
tr	Response Time	$RL = 1 K\Omega VR = 50V$		25		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz [FORM NO. 100-PDB-C112 REV A]